RX-0005



- InGaAs PIN Diode
- High bandwidth

Performance Highlights

- Responsivity typically 0.8A/W at 1300nm Maximum dark current of 5nA
- Bandwidth of 1.5GHz

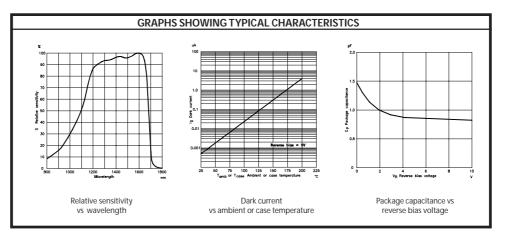
LIMITING VALUES	SYMBOL	VALUE	UNITS
Continuous reverse voltage	V _R	30	V
Forward current	I _F	5	mA
Reverse current	I _R	5	mA
Operating temperature	T _{amb}	-40 to +85	°C
Storage temperature	T _{stg}	-40 to +85	°C
Soldering temperature 2mm from case for 10s	T _{sld}	250	°C

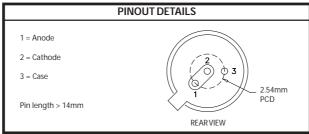
OPTICAL/ELECTRICAL CHARACTERISTICS	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITION
Responsivity (1)	R	0.7			A/W	$\lambda = 1300$ nm, $V_R = 5V$
Rise time	t _r			0.5	ns	$V_R = 5V$
Fall time	t _f			0.5	ns	$V_R = 5V$
Operating voltage	V _R			20	V	
Capacitance	C _T			0.9	pF	$V_R = 5V, f = 1MHz$
Dark current	I _D	·	0.5	5.0	nA	$V_R = 5V$

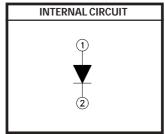
All values apply at a temperature of 25°C

Applies when using a 50/125µm fibre









NOTES:

1) The device is very susceptible to damage by electrostatic discharge.